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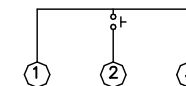
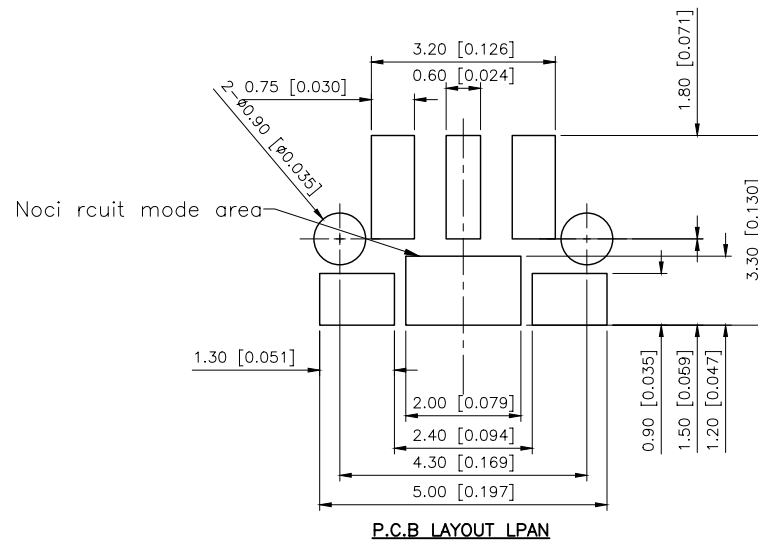
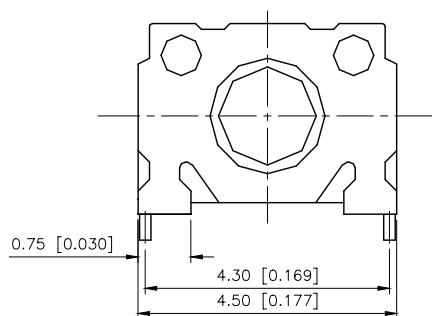
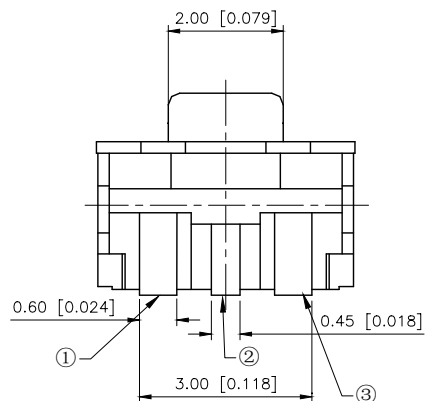
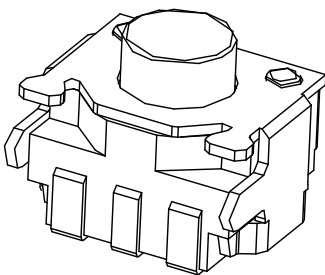
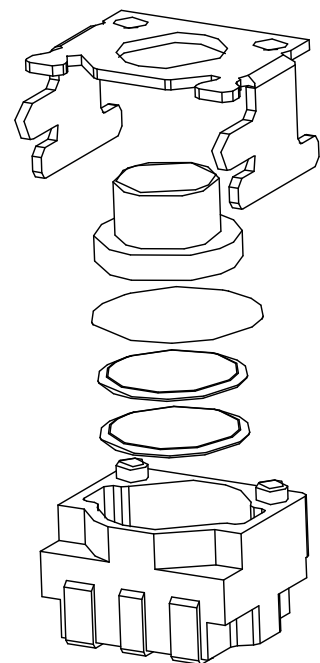
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REVISIONS					
REV.	ECN NO.	LOCATION	DESCRIPTION	DATE	DESIGN
A0	N/A		INITIAL RELEASE	/	/
A1	N/A		图面升级整理图面	2025.06.04	阿树



CIRCUIT DIAGRAM

SPECIFICATION
Contact Rating: 50mA,12V DC
Contact Resistance: 100mΩ max
Insulation Resistance: 100MΩ min.500V DC
Dielectric Strength: 250V AC/1minute
Travel: 0.20mm
Operating Temp: -30℃~+85℃
Storage Temp: -30℃~+80℃

PAPT NO	TS-1133-B-B
Operating Force	A:100gf B:160gf C:260gf
Keystake	A:PA46 B:Silica gel

⑤	Terminal	3	Brass (0.30t)	Plating silvering
④	Contact	1	F.ag/SUS	Natural
③	Base	1	Pa46	
②	Cover	1	Spcc	Plating Nickel
①	Keystake	1	Silica gel	
ITEM	PAPT NAMF	QTY	MATERIAL	FINISHING

AuGLAR	±5°
X.	±0.40
X.x	±0.30
X.xx	±0.20
X.xxx	±0.15
UNSPECIFIED TOLERAuCES	



DESIGN	阿树	VIEW:		MODEL TYPE:	TACT SWITCH
CHECKED		UNIT:	mm/in	PART NO.:	TS-1133-B-B
APPROVED		SIZE:	A4	DWG NO.:	TS-1133-B-B

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